

AMENDMENTS TO THE CLAIMS:

Please cancel claims 13 and 17 without prejudice or disclaimer.

1. (Previously presented) A liquid crystal display device, comprising:
 - a plurality of pixels arranged in a matrix form, each of said pixels comprising:
 - a pixel electrode formation area wherein a pixel electrode is formed; and
 - a thin film transistor formation area wherein a thin film transistor is formed and connected to said pixel electrode, said thin film transistor comprising:
 - a semiconductor layer serving as a channel;
 - a terminal formed to be connected to said pixel electrode;
 - a passivation layer formed to cover said thin film transistor; and
 - an organic insulating layer covering said passivation layer,
 - wherein said pixel electrode formation area comprises a plurality of prism-shaped base posts, and an uneven layer formed on said plurality of prism-shaped base posts, wherein said semiconductor layer extends from said channel toward said pixel electrode formation area beyond said terminal and terminated in said pixel electrode formation area to form a termination end that is aligned with a termination end of said passivation layer, and
 - wherein said organic insulating layer covers said termination ends of said semiconductor layer and said passivation layer.
2. (Original) The device as claimed in claim 1, wherein said pixel electrode is connected to said terminal of said thin film transistor through a contact hole that is selectively formed in said organic insulating layer and said passivation layer.
3. (Previously presented) The device as claimed in claim 1, wherein said uneven layer covers said plurality of prism-shaped base posts and is formed between said plurality of prism-shaped base posts.
4. (Previously presented) The device as claimed in claim 1, wherein said pixel electrode comprises a reflection-type electrode which is formed on said uneven layer.

5. (Previously presented) The device as claimed in claim 6, wherein said pixel electrode comprises a shape which follows a contour of said uneven layer.
6. (Previously presented) The device as claimed in claim 1, wherein said uneven layer comprises a transparent photosensitive resist.
7. (Previously presented) The device as claimed in claim 1, wherein said pixel electrode comprises one of sputtered aluminum and sputtered silver.
8. (Previously presented) The device as claimed in claim 1, further comprising:
a transparent insulating substrate, said plurality of prism-shaped base posts being formed on said transparent insulating substrate.
9. (Previously presented) The device as claimed in claim 8, wherein said thin film transistor further comprises a gate insulation film formed on said transparent insulating substrate.
10. (Previously presented) The device as claimed in claim 9, wherein said plurality of prism-shaped base posts comprise:
an insulation film formed on said transparent substrate;
a semiconductor film formed on said insulation layer; and
an inorganic insulating film formed on said semiconductor layer.
11. (Previously presented) The device as claimed in claim 10, wherein said insulation film, said semiconductor film, and said inorganic insulating film are formed concurrently with a formation of said gate insulation film, said semiconductor layer and said passivation film in said thin film transistor, respectively.
12. (Previously presented) The device as claimed in claim 1, wherein said thin film transistor further comprises a drain electrode, said pixel electrode being connected to said drain electrode.

drain electrode via a contact through hole formed in said uneven layer, and a contact through hole passing through said passivation layer.

13. (Cancelled)

14. (Currently amended) A thin film transistor array substrate for a liquid crystal display device, said thin film transistor substrate comprising:

an insulating substrate;

a plurality of data lines formed on said insulating substrate;

a plurality of gate lines formed on said insulating substrate, such that areas bounded by said plurality of gate lines and said plurality of data lines define a plurality of pixels in said liquid crystal display device;

a plurality of thin film transistors respectively formed on said insulating substrate in said plurality of pixels;

a plurality of prism-shaped base posts formed adjacent to a thin film transistor in each of said plurality of pixels;

an uneven layer formed on said plurality of prism-shaped base posts; and

a pixel electrode formed on said uneven layer,

~~The thin film transistor array substrate according to claim 13,~~

wherein said thin film transistor comprises:

a gate insulation layer formed on said transparent insulating substrate;

a semiconductor layer formed on said gate insulation layer; and

a passivation layer formed on said semiconductor layer.

15. (Previously presented) The device as claimed in claim 14, wherein said plurality of prism-shaped base posts comprises:

an insulation film formed on said transparent substrate;

a semiconductor film formed on said insulation layer; and

an inorganic insulating film formed on said semiconductor layer.

16. (Previously presented) The device as claimed in claim 15, wherein said insulation

film, said semiconductor film, and said inorganic insulating film are formed concurrently with a formation of said gate insulation layer, said semiconductor layer and said passivation layer in said thin film transistor, respectively.

17. (Canceled)

18. (Currently amended) A method of forming a thin film transistor array substrate for a liquid crystal display device, comprising:

forming a plurality of data lines on a insulating substrate;

forming a plurality of gate lines on said insulating substrate, such that areas bounded by said plurality of gate lines and said plurality of data lines define a plurality of pixels in said liquid crystal display device;

forming a plurality of thin film transistors respectively on said insulating substrate in said plurality of pixels;

forming a plurality of prism-shaped base posts adjacent to a thin film transistor in each of said plurality of pixels;

forming an uneven layer on said plurality of prism-shaped base posts; and

forming a pixel electrode formed on said uneven layer,

The method according to claim 17,

wherein said forming said plurality of thin film transistors comprises:

forming a gate insulation layer on said transparent insulating substrate;

forming a semiconductor layer on said gate insulation layer; and

forming a passivation layer on said semiconductor layer.

19. (Previously presented) The device as claimed in claim 18, wherein said forming said plurality of prism-shaped base posts comprises:

forming an insulation film on said transparent substrate;

forming a semiconductor film on said insulation layer; and

forming an inorganic insulating film on said semiconductor layer.

20. (Previously presented) The device as claimed in claim 19, wherein said forming said

insulation film, forming said semiconductor film, and forming said inorganic insulating film are performed concurrently with said forming said gate insulation layer, forming said semiconductor layer and forming said passivation layer in said thin film transistor, respectively.